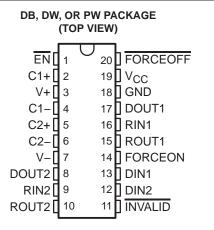
## SN65C3223, SN75C3223 3-V TO 5.5-V MULTICHANNEL RS-232 COMPATIBLE LINE DRIVER/RECEIVER

SLLS538B - JUNE 2002 - REVISED OCTOBER 2004

- Operate With 3-V to 5.5-V V<sub>CC</sub> Supply
- Operate Up To 1 Mbit/s
- Low Standby Current . . . 1 μA Typ
- External Capacitors . . . 4 × 0.1 μF
- Accept 5-V Logic Input With 3.3-V Supply
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)
- Applications
  - Battery-Powered Systems, PDAs, Notebooks, Laptops, Palmtop PCs, and Hand-Held Equipment



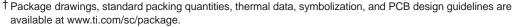
#### description/ordering information

The SN65C3223 and SN75C3223 consist of two line drivers, two line receivers, and a dual charge-pump circuit with  $\pm 15$ -kV ESD protection pin to pin (serial-port connection pins, including GND). The devices provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at data signaling rates up to 1 Mbit/s and a driver output slew rate of 24 V/ $\mu$ s to 150 V/ $\mu$ s

Flexible control options for power management are available when the serial port is inactive. The auto-powerdown feature functions when FORCEON is low and FORCEOFF is high. During this mode of operation, if the device does not sense a valid RS-232 signal, the driver outputs are disabled. If FORCEOFF is set low and  $\overline{\text{EN}}$  is high, both drivers and receivers are shut off, and the supply current is reduced to 1  $\mu$ A. Disconnecting the serial port or turning off the peripheral drivers causes auto-powerdown to occur. Auto-powerdown can be disabled when FORCEON and FORCEOFF are high. With auto-powerdown enabled, the device is activated automatically when a valid signal is applied to any receiver input. The INVALID output is used to notify the user if an RS-232 signal is present at any receiver input. INVALID is high (valid data) if any receiver input voltage is greater than 2.7 V or less than -2.7 V or has been between -0.3 V and 0.3 V for less than 30  $\mu$ s. INVALID is low (invalid data) if the receiver input voltage is between -0.3 V and 0.3 V for more than 30  $\mu$ s. Refer to Figure 4 for receiver input levels.

#### ORDERING INFORMATION

TA	PACKAG	GE <sup>†</sup>	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	2010 DW	Tube of 25	SN75C3223DW	7500000
	SOIC – DW	Reel of 2000	SN75C3223DWR	75C3223
0°C to 70°C	SSOP - DB	Reel of 2000	SN75C3223DBR	CA3223
		Tube of 70	SN75C3223PW	0.1000
	TSSOP – PW	Reel of 2000	SN75C3223PWR	CA3223
	2010 5141	Tube of 25	SN65C3223DW	050000
	SOIC – DW	Reel of 2000	SN65C3223DWR	65C3223
-40°C to 85°C	SSOP - DB	Reel of 2000	SN65C3223DBR	CB3223
	T000D DW	Tube of 70	SN65C3223PW	00000
	TSSOP - PW	Reel of 2000	SN65C3223PWR	CB3223



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





#### **Function Tables**

#### **EACH DRIVER**

		INPUTS		OUTPUT	
DIN	FORCEON	FORCEOFF	VALID RIN RS-232 LEVEL	DOUT	DRIVER STATUS
Х	Χ	L	Х	Z	Powered off
L	Н	Н	Х	Н	Normal operation with
Н	Н	Н	X	L	auto-powerdown disabled
L	L	Н	Yes	Н	Normal operation with
Н	L	Н	Yes	L	auto-powerdown enabled
L	L	Н	No	Z	Powered off by
Н	L	Н	No	Z	auto-powerdown feature

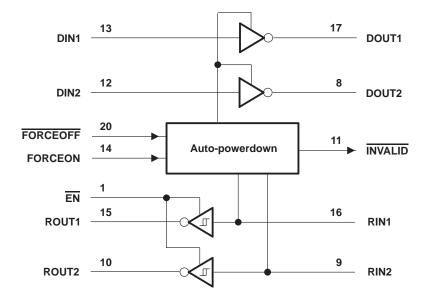
H = high level, L = low level, X = irrelevant, Z = high impedance

#### **EACH RECEIVER**

	INP	PUTS	OUTPUT
RIN	EN	VALID RIN RS-232 LEVEL	ROUT
L	L	Х	Н
Н	L	X	L
X	Н	X	Z
Open	L	No	Н

H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = input disconnected or connected driver off

### logic diagram (positive logic)



## SN65C3223, SN75C3223 3-V TO 5.5-V MULTICHANNEL RS-232 COMPATIBLE LINE DRIVER/RECEIVER

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## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub> (see Note 1)	0.3 V to 6 V
Positive output supply voltage range, V+ (see Note 1)	–0.3 V to 7 V
Negative output supply voltage range, V– (see Note 1)	0.3 V to –7 V
Supply voltage difference, V+ – V– (see Note 1)	13 V
Input voltage range, V <sub>I</sub> : Driver, FORCEOFF, FORCEON, EN	–0.3 V to 6 V
Receiver	–25 V to 25 V
Output voltage range, VO: Driver	
Receiver, INVALID	$-0.3 \text{ V to V}_{CC} + 0.3 \text{ V}$
Package thermal impedance, θ <sub>JA</sub> (see Notes 2 and 3): DB package	70°C/W
DW package	58°C/W
PW package	83°C/W
Operating virtual junction temperature, T <sub>J</sub>	150°C
Storage temperature range, T <sub>stq</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to network GND.

- 2. Maximum power dissipation is a function of T<sub>J</sub>(max), θ<sub>JA</sub>, and T<sub>A</sub>. The maximum allowable power dissipation at any allowable ambient temperature is P<sub>D</sub> = (T<sub>J</sub>(max) T<sub>A</sub>)/θ<sub>JA</sub>. Operating at the absolute maximum T<sub>J</sub> of 150°C can affect reliability.
- 3. The package thermal impedance is calculated in accordance with JESD 51-7.

## recommended operating conditions (see Note 4 and Figure 6)

				MIN	NOM	MAX	UNIT
.,	Owner hower Heavier		V <sub>CC</sub> = 3.3 V	3	3.3	3.6	.,
VCC	Supply voltage		$V_{CC} = 5 V$	4.5	5	5.5	V
V	Deliver and control bink level innertweltens	DIN, EN, FORCEOFF,	V <sub>CC</sub> = 3.3 V	2			.,
VIH	Driver and control high-level input voltage	FORCEON	$V_{CC} = 5 V$	2.4			V
V <sub>IL</sub>	Driver and control low-level input voltage	DIN, EN, FORCEOFF, FORCE	ON			0.8	V
V	Driver and control input voltage	DIN, EN, FORCEOFF, FORCE	ON	0		5.5	
VI	Receiver input voltage			-25		25	V
т.	Operating free air temperature		SN65C3223	-40		85	°C
TA	Operating free-air temperature		SN65C3223	0		70	C

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3  $V \pm 0.3$  V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5  $V \pm 0.5$  V.

# electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

-	•	, ,	• ,				
	PARA	METER	TEST CONDITIONS	MIN	TYP‡	MAX	UNIT
II	Input leakage current	EN, FORCEOFF, FORCEON			±0.01	±1	μΑ
		Auto-powerdown disabled	No load, FORCEOFF, FORCEON at V <sub>CC</sub>		0.3	1	mA
Icc	Supply current	Powered off	No load, FORCEOFF at GND		1	10	
	очрену очнотк	Auto-powerdown enabled	No load, FORCEOFF at V <sub>CC</sub> , FORCEON at GND, All RIN are open or grounded		1	10	μΑ

<sup>‡</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.



#### **DRIVER SECTION**

#### electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

	PARAMETER	TE	ST CONDITION:	S	MIN	TYP†	MAX	UNIT
Vон	High-level output voltage	DOUT at R <sub>L</sub> = $3 \text{ k}\Omega$ to G	ND		5	5.4		V
VOL	Low-level output voltage	DOUT at R <sub>L</sub> = $3 \text{ k}\Omega$ to G	ND		-5	-5.4		V
lн	High-level input current	VI = VCC				±0.01	±1	μΑ
Ι <sub>Ι</sub> L	Low-level input current	V <sub>I</sub> at GND				±0.01	±1	μΑ
	Object singuity autout assessed	V <sub>CC</sub> = 3.6 V,	VO = 0 V			±35	±60	A
los	Short-circuit output current‡	V <sub>CC</sub> = 5.5 V,	VO = 0 V			±35	±90	mA
r <sub>O</sub>	Output resistance	$V_{CC}$ , V+, and V- = 0 V,	V <sub>O</sub> = ±2 V		300	10M		Ω
	Output lookage current	FORCEOFF = GND	$V_0 = \pm 12 V$ ,	V <sub>CC</sub> = 3 V to 3.6 V			±25	
loff	Output leakage current	FORGEOFF = GND	$V_0 = \pm 10 \text{ V},$	V <sub>CC</sub> = 4.5 V to 5.5 V			±25	μΑ

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

#### switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

	PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
			C <sub>L</sub> = 1000 pF		250			
	Maximum data rate (see Figure 1)	$R_L = 3 k\Omega$ , One DOUT switching	C <sub>L</sub> = 250 pF,	$V_{CC} = 3 V \text{ to } 4.5 V$	1000			kbit/s
	(SSS 1 iguilo 1)	one boot ewitering	C <sub>L</sub> = 1000 pF,	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	1000			
tsk(p)	Pulse skew§	C <sub>L</sub> = 150 pF to 2500 pF,	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$	See Figure 2		300		ns
SR(tr)	Slew rate, transition region (see Figure 1)	$V_{CC}$ = 3.3 V, R <sub>L</sub> = 3 kΩ to 7 kΩ	C <sub>L</sub> = 150 pF to 1000	pF	18		150	V/μs

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

\$ Pulse skew is defined as  $|tp_{LH} - tp_{HL}|$  of each channel of the same device. NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V ± 0.5 V.



<sup>‡</sup> Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.

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#### RECEIVER SECTION

# electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>†</sup>	MAX	UNIT
Vон	High-level output voltage	$I_{OH} = -1 \text{ mA}$	V <sub>CC</sub> - 0.6	V <sub>CC</sub> - 0.1		V
VOL	Low-level output voltage	I <sub>OL</sub> = 1.6 mA			0.4	V
\/-	Decisive region invest three health value	V <sub>CC</sub> = 3.3 V		1.6	2.4	V
V <sub>IT+</sub>	Positive-going input threshold voltage	V <sub>CC</sub> = 5 V		1.9	2.4	V
	Manadan as a sand through all college	V <sub>CC</sub> = 3.3 V	0.6	1.1		
$V_{IT-}$	Negative-going input threshold voltage	V <sub>CC</sub> = 5 V	0.8	1.4		V
V <sub>hys</sub>	Input hysteresis (V <sub>IT+</sub> - V <sub>IT-</sub> )			0.5		V
l <sub>off</sub>	Output leakage current	EN = V <sub>CC</sub>		±0.05	±10	μΑ
rį	Input resistance	$V_I = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

 $<sup>\</sup>dagger$  All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C.

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

# switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4)

	PARAMETER	TEST (	CONDITIONS	MIN TYPT	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output	C <sub>L</sub> = 150 pF,	See Figure 3	150		ns
t <sub>PHL</sub>	Propagation delay time, high- to low-level output	C <sub>L</sub> = 150 pF,	See Figure 3	150		ns
ten	Output enable time	C <sub>L</sub> = 150 pF, See Figure 4	$R_L = 3 \text{ k}\Omega$ ,	200		ns
<sup>t</sup> dis	Output disable time	C <sub>L</sub> = 150 pF, See Figure 4	$R_L = 3 \text{ k}\Omega$ ,	200		ns
t <sub>sk(p)</sub>	Pulse skew <sup>‡</sup>	See Figure 3		50		ns

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25 ^{\circ}\text{C}$ .

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.



<sup>‡</sup> Pulse skew is defined as |tpLH - tpHL| of each channel of the same device.

#### **AUTO-POWERDOWN SECTION**

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

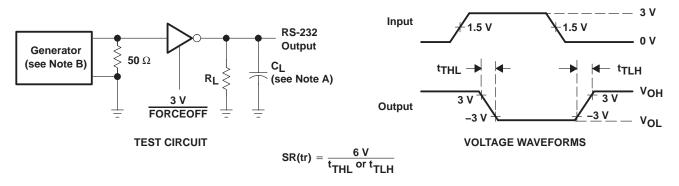
	PARAMETER	TEST C	ONDITIONS	MIN	MAX	UNIT
VT+(valid)	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	FORCEOFF = V <sub>CC</sub>		2.7	V
V <sub>T</sub> –(valid)	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	FORCEOFF = V <sub>CC</sub>	-2.7		V
V <sub>T</sub> (invalid)	Receiver input threshold for INVALID low-level output voltage	FORCEON = GND,	FORCEOFF = V <sub>CC</sub>	-0.3	0.3	V
Vон	INVALID high-level output voltage	I <sub>OH</sub> = -1 mA, FORCEOFF = V <sub>CC</sub>	FORCEON = GND,	V <sub>CC</sub> - 0.6	·	V
VOL	INVALID low-level output voltage	I <sub>OL</sub> = 1.6 mA, FORCEOFF = V <sub>CC</sub>	FORCEON = GND,		0.4	V

# switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	alid Propagation delay time, high- to low-level output		UNIT
<sup>t</sup> valid	Propagation delay time, low- to high-level output	1	μs
<sup>t</sup> invalid	Propagation delay time, high- to low-level output	30	μs
t <sub>en</sub>	Supply enable time	100	μs

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

#### PARAMETER MEASUREMENT INFORMATION

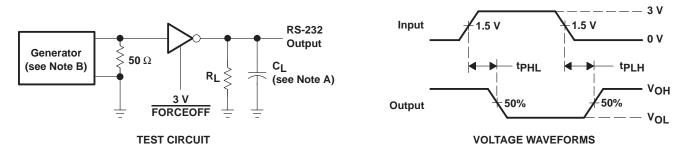


NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_O = 50~\Omega$ , 50% duty cycle,  $t_\Gamma \le 10$  ns.  $t_f \le 10$  ns.

Figure 1. Driver Slew Rate

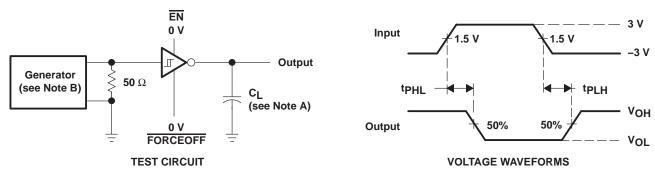
#### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_f \le 10$  ns.  $t_f \le 10$  ns.

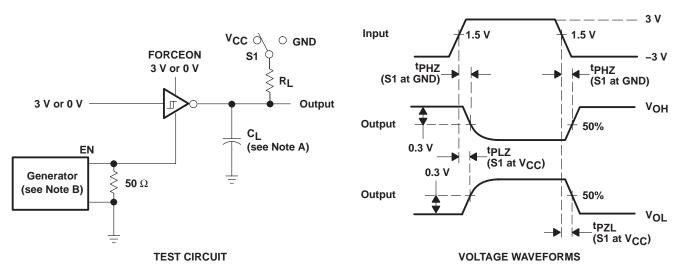
Figure 2. Driver Pulse Skew



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics:  $Z_O = 50~\Omega$ , 50% duty cycle,  $t_\Gamma \le 10~\text{ns}$ .  $t_f \le 10~\text{ns}$ .

Figure 3. Receiver Propagation Delay Times



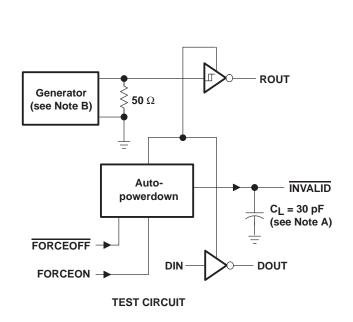
NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

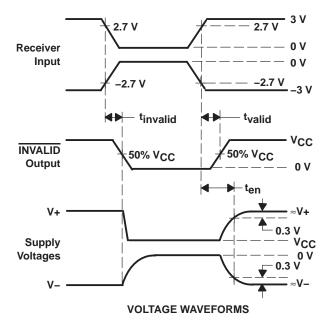
B. The pulse generator has the following characteristics:  $Z_O = 50 \ \Omega$ , 50% duty cycle,  $t_f \le 10 \ ns$ ,  $t_f \le 10 \ ns$ .

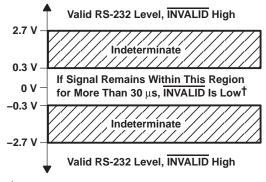
Figure 4. Receiver Enable and Disable Times



#### PARAMETER MEASUREMENT INFORMATION







 $<sup>\</sup>dagger$  Auto-powerdown disables drivers and reduces supply current to 1  $\mu$ A.

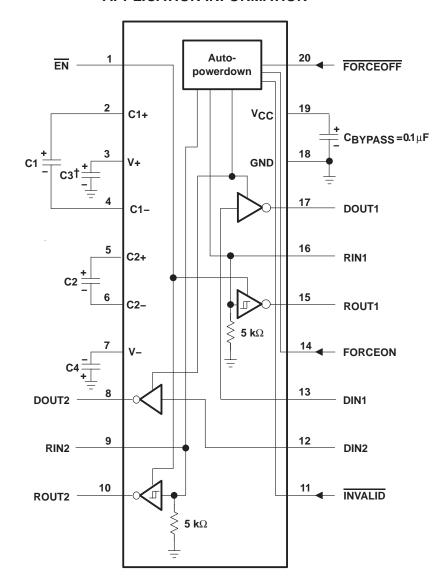
NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 5 kbit/s,  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_f \le 10$  ns.  $t_f \le 10$  ns.

Figure 5. INVALID Propagation Delay Times and Supply Enabling Time



#### **APPLICATION INFORMATION**



†C3 can be connected to V<sub>CC</sub> or GND. NOTE A: Resistor values shown are nominal.

#### V<sub>CC</sub> vs CAPACITOR VALUES

VCC	C1	C2, C3, C4
$\begin{array}{c} \textbf{3.3 V} \pm \textbf{0.3 V} \\ \textbf{5 V} \pm \textbf{0.5 V} \\ \textbf{3 V to 5.5 V} \end{array}$	0.1 μF 0.047 μF 0.1 μF	0.1 μF 0.33 μF 0.47 μF

Figure 6. Typical Operating Circuit and Capacitor Values





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#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65C3223DBR	LIFEBUY	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3223	
SN65C3223DW	LIFEBUY	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3223	
SN75C3223DBR	LIFEBUY	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3223	
SN75C3223DWR	LIFEBUY	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3223	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# **PACKAGE OPTION ADDENDUM**

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

# **PACKAGE MATERIALS INFORMATION**

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#### TAPE AND REEL INFORMATION



# TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

	· · · · · · · · · · · · · · · · · · ·
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3223DBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN65C3223PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
SN75C3223DBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN75C3223DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN75C3223PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1



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#### \*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3223DBR	SSOP	DB	20	2000	356.0	356.0	35.0
SN65C3223PWR	TSSOP	PW	20	2000	356.0	356.0	35.0
SN75C3223DBR	SSOP	DB	20	2000	356.0	356.0	35.0
SN75C3223DWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN75C3223PWR	TSSOP	PW	20	2000	356.0	356.0	35.0

# **PACKAGE MATERIALS INFORMATION**

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#### **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65C3223DW	DW	SOIC	20	25	507	12.83	5080	6.6
SN65C3223PW	PW	TSSOP	20	70	530	10.2	3600	3.5
SN75C3223PW	PW	TSSOP	20	70	530	10.2	3600	3.5



SMALL OUTLINE PACKAGE



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SOIC



#### NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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